

Silicon NPN Power Transistors

2SD1497

DESCRIPTION

- With TO-3PN package
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- High voltage power switching TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

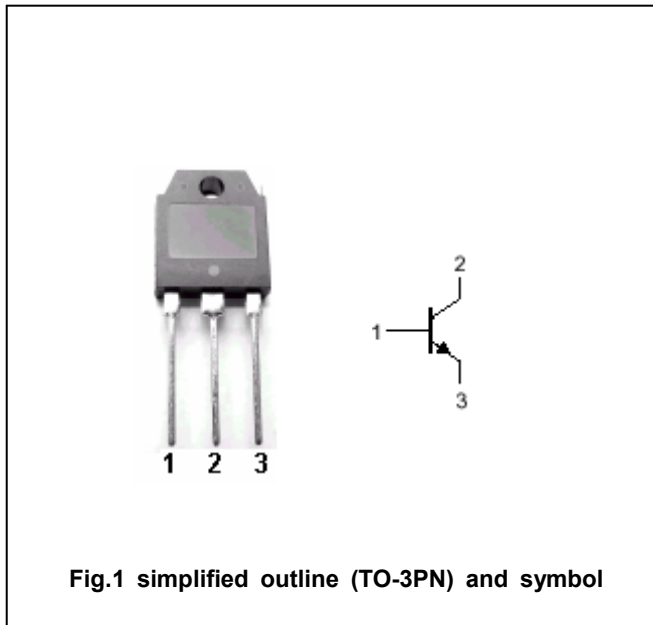


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		6	A
I _{CM}	Collector current-peak		7	A
I _{C(surge)}	Collector surge current		16	A
P _C	Collector power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-45~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	7			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; R _{BE} =∞	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =1A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1A			1.5	V
I _{CEx}	Collector cut-off current	V _{CE} =1500V; V _{BE} =1.5V			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =0.3A; V _{CE} =5V	10		30	
h _{FE-2}	DC current gain	I _C =5A; V _{CE} =5V	5			
t _f	Fall time	I _{CP} =4A; I _{B1} =1.3A; L _B =0			2.0	μs

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PACKAGE OUTLINE

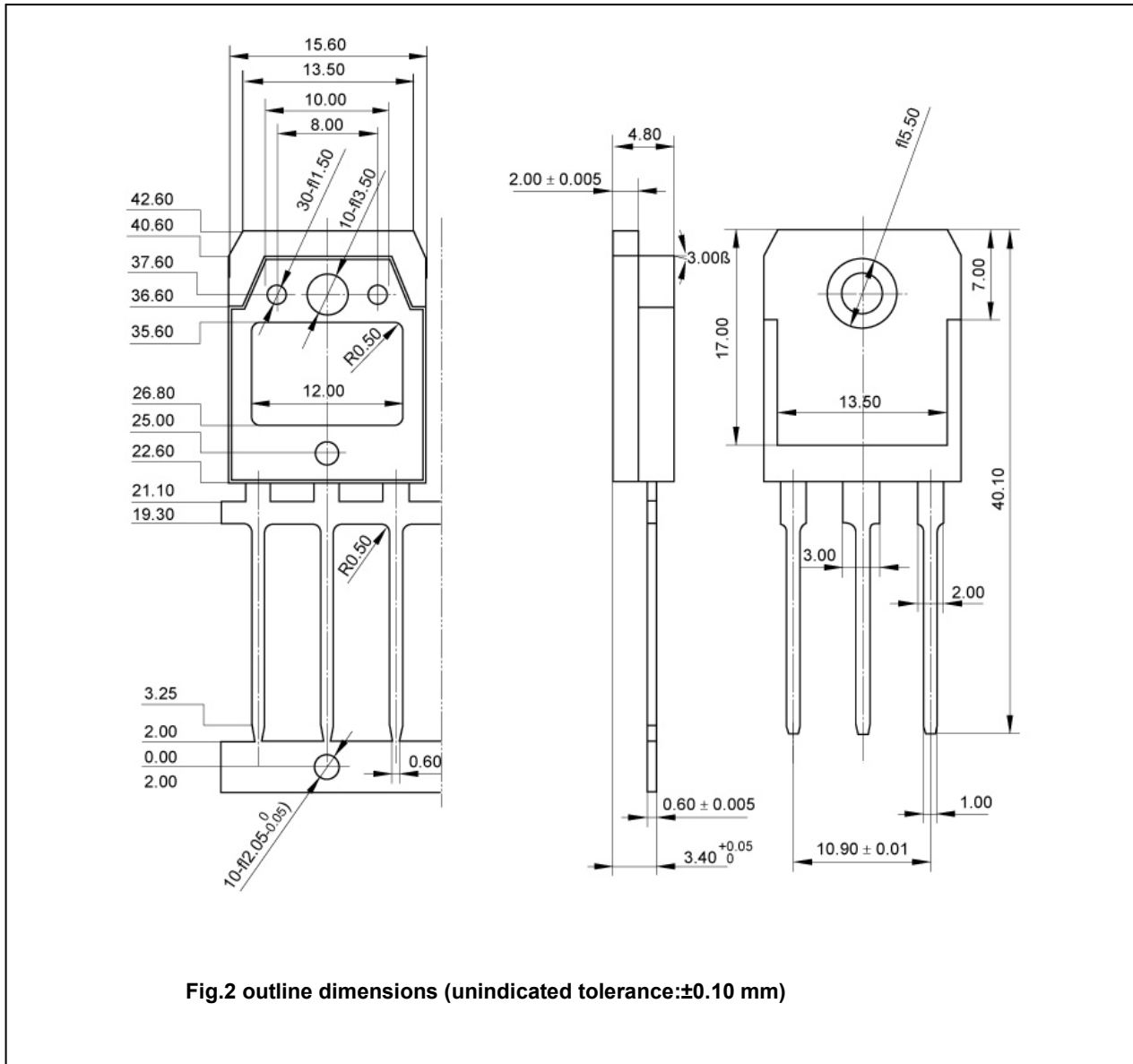


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)